

## 75V N-Channel Power MOSFET



# TO-220

#### Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

#### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)	
75	8 @ V <sub>GS</sub> =10V	80	

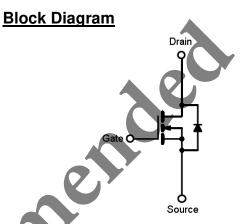
#### **Features**

- Advanced Trench Technology
- Low  $R_{DS(ON)} 8m\Omega$  (Max.)
- Low gate charge typical @ 91.5nC (Typ.)
- Low Crss typical @ 203pF (Typ.)

#### **Ordering Information**

Part No.	Package	Packing
TSM80N08CZ C0G	TO-220	50pcs / Tube

Note: "G" denotes for Halogen Free



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	75	V	
Gate-Source Voltage		$V_{GS}$	±25	V	
	T <sub>c</sub> =25°C	l <sub>D</sub>	80	A	
Continuous Drain Current	T <sub>C</sub> =70°C		60		
Continuous Drain Current	T <sub>A</sub> =25°C		12	A	
	T <sub>A</sub> =70°C		9		
Drain Current-Pulsed Note 1		$I_{DM}$	320	Α	
Avalanche Current, L=0.3mH		I <sub>AS</sub>	35	Α	
Avalanche Energy, L=0.3mH		E <sub>AS</sub>	183	mJ	
	T <sub>C</sub> =25°C		113.6		
Maximum Power Dissipation	T <sub>C</sub> =70°C	P <sub>D</sub>	72.7	W	
Waxiinum Power Dissipation	T <sub>A</sub> =25°C		2		
	T <sub>A</sub> =70°C		1.3		
Storage Temperature Range		$T_{STG}$	-55 to +150	ô	
Operating Junction Temperature Range		$T_J$	-55 to +150	°C	

<sup>\*</sup> Limited by maximum junction temperature

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	$R\Theta_{JC}$	1.1	°C/W
Thermal Resistance - Junction to Ambient	$R\Theta_{JA}$	62.5	°C/W

Notes: Surface mounted on FR4 board t ≤ 10sec



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**Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV <sub>DSS</sub>	75			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 40A$	R <sub>DS(ON)</sub>		6	8	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	2	3	4	٧
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	I <sub>DSS</sub>		🛦	1	uA
Gate Body Leakage	$V_{GS} = \pm 25V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Dynamic						
Total Gate Charge	V 00V I 40A	$Q_g$		91.5		
Gate-Source Charge	$V_{DS} = 30V, I_D = 40A,$	$Q_{gs}$		34		nC
Gate-Drain Charge	$V_{GS} = 10V$	$Q_{gd}$		19.9		
Input Capacitance	.,	C <sub>iss</sub>		3905		
Output Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$	Coss		371		рF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>	7	203		
Switching						
Turn-On Delay Time		$t_{d(on)}$		21.5		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 30V,$	t <sub>r</sub>		11		C
Turn-Off Delay Time	ID = 1A, $R_G = 3.3\Omega$	t <sub>d(off)</sub>		73		nS
Turn-Off Fall Time		t <sub>f</sub>		66		
Drain-Source Diode Characteristics and Maximum Rating						
Drain-Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	V <sub>SD</sub>	-	0.8	1.3	٧
Reverse Recovery Time	I <sub>S</sub> = 40A, T <sub>J</sub> =25 °C	t <sub>fr</sub>		36		nS
Reverse Recovery Charge	dl/dt = 100A/us	$Q_{fr}$		45		nC

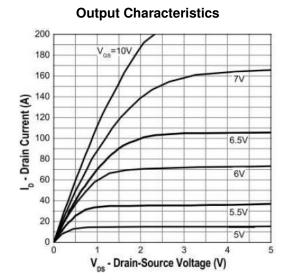
- Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
  Rθ<sub>JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Rθ<sub>JC</sub> is guaranteed by design while Rθ<sub>CA</sub> is determined by the user's board design. Rθ<sub>JA</sub> shown below for single device operation on FR-4 in still air



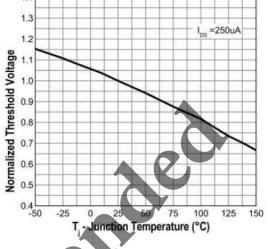
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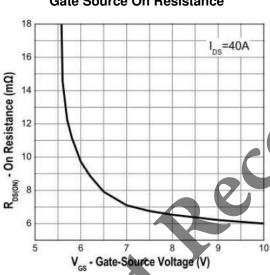
**Electrical Characteristics Curve** (Ta = 25°C, unless otherwise noted)



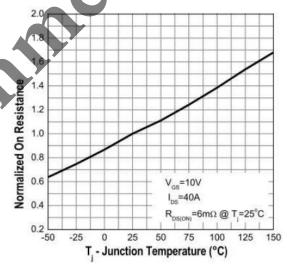
**Gate Threshold Voltage** 



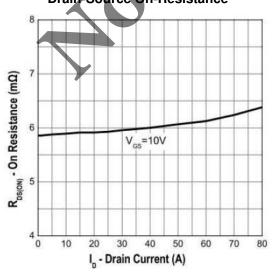
**Gate Source On Resistance** 



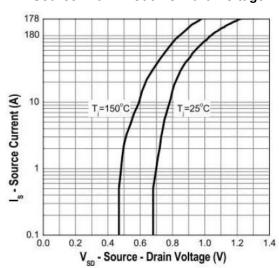
**Drain-Source On Resistance** 







#### Source-Drain Diode Forward Voltage

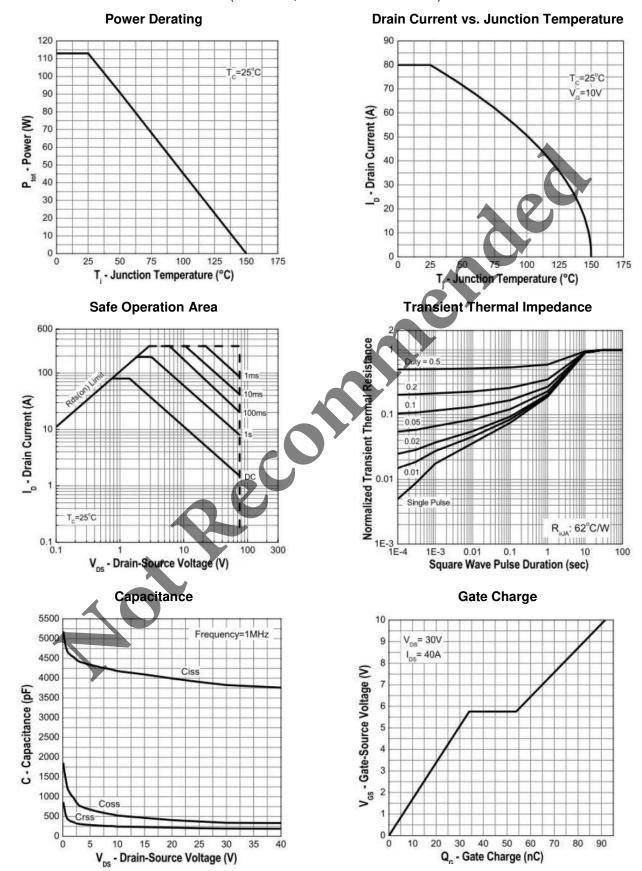




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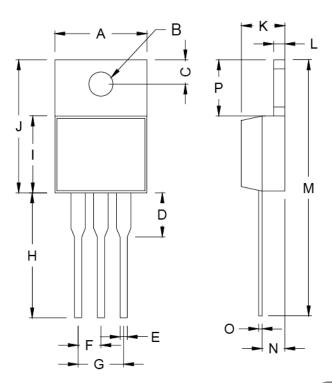




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## **TO-220 Mechanical Drawing**

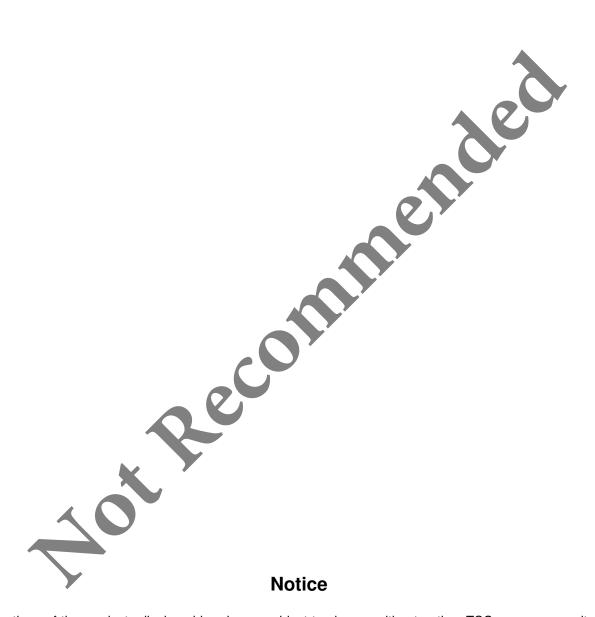


TO-220 DIMENSION						
DIM	MILLIMETERS		INCHES			
וווט	MIN	MAX	MIN	MAX		
Α	10.000	10.500	0.394	0.413		
В	3.740	3.910	0.147	0.154		
С	2.440	2.940	0.096	0.116		
D	-	6.350		0.250		
Е	0.381	1.106	0.015	0.040		
F	2.345	2.715	0.092	0.058		
G	4.690	5.430	0.092	0.107		
Н	12.700	14.732	0.500	0.581		
J	14.224	16.510	0.560	0.650		
K	3.556	4.826	0.140	0.190		
L	0.508	1.397	0.020	0.055		
М	27.700	29.620	1.060	1.230		
N	2.032	2.921	0.080	0.115		
0	0.255	0.610	0.010	0.024		
P	5.842	6.858	0.230	0.270		



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